

ABSTRACT

Method of fabricating thin-film transistors in which contact with connecting electrodes becomes reliable. When contact holes are formed, the bottom insulating layer is subjected to a wet etching process, thus
5 producing undercuttings inside the contact holes. In order to remove the undercuttings, a light etching process is carried out to widen the contact holes. Thus, tapering section are obtained, and the covering of connection wiring is improved.